Direct-recombination electron emission from 3d excitation in Ce

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The first observation of 3d direct-recombination electron emission in the rare earths is reported. The $3d^94f^2$ state of Ce is induced by electron excitation, and $3d^94f^2 \rightarrow 3d^{10}4f^0 + \epsilon l$ electron emission is observed at energies above the main Auger decay channels. The interpretation is confirmed by comparison with emission from La, in which such processes cannot occur. CeO₂ behaves in a similar manner to Ce metal, supporting suggestions of a $4f^2$ configuration contribution in the final state following 3d excitation.

In the rare earths both x-ray- and electron-induced excitations from 3d and 4d levels to empty 4f states are known to be highly localized in character. In the case of 4d excitation the presence of final-state multiplet structure characteristic of $4d^{10}4f^n \rightarrow 4d^94f^{n+1}$ transitions is well established. For 3d excitation the multiplet structure is somewhat less prominent, but atomic behavior can clearly be inferred from the fact that the absorption energies are *less* than the 3d x-ray photoelectron spectroscopy (XPS) energies and are insensitive to environment for a given 4f population.¹ Electron-energy-loss spectroscopy reveals additional 3d excitation structure not observed in x-ray absorption,² and Matthew *et al.*³ have recently interpreted these features as additional $3d^94f^{n+1}$ multiplet states which are not dipole allowed.

Atomiclike behavior may be further confirmed by monitoring the decay of the excited state. In the case of 4dexcitation by monochromatic synchrotron-radiation resonant enhancement of photoemission from weakly bound electron states is observed, corresponding to direct-recombination processes such as

$$4d^{9}5s^{2}5p^{6}4f^{n+1}V \rightarrow 4d^{10}5s^{2}5p^{6}4f^{n-1}V + \epsilon l \rightarrow 4d^{10}5s^{2}5p^{6}4f^{n}V^{-1} + \epsilon l \rightarrow 4d^{10}5s^{2}5p^{5}4f^{n}V + \epsilon l \rightarrow 4d^{10}5s^{1}5p^{6}4f^{n}V + \epsilon l , \qquad (1)$$

which have been widely observed.⁴⁻⁶

Under electron excitation both Auger emission from ionized atoms and direct-recombination emission occur, and Matthew and Girvin⁷ have shown that, for reasonably high incident energy, the electron-stimulated emission corresponds to an integral of the photon-stimulated yield over all photon energies, and as a result the directrecombination yield may become masked by Auger emission in the same energy region. Where the main excitation is significantly above the 4*d* ionization threshold one direct-recombination channel will emit at energies well above the main Auger channel, and direct recombination may then be unambiguously identified,⁸⁻¹¹ conditions that appear to be satisfied on all the rare earths up to Tb. In addition, Hoogewijs *et al.*¹² have recently seen weak resonant electron emission from heavily oxidized La due to

$$4d^{9}4f^{1}V \to 4d^{10}4f^{0}V^{-1}$$
 (2)

direct recombination, with V corresponding here to the mainly O 2p valence band, i.e., an interatomic direct-recombination process.

For 3d excitations resonant photoemission is much more difficult because of the higher binding energy involved, so that Esteva et al.¹³ have only been able to measure the electron yield as a function of photon energy, and to correlate the results with 3d absorption in La and Gd. Chamberlain et al.¹⁴ and Connerade and Karnatak¹⁵ have, however, observed resonant $3d^{9}4f^{n+1} \rightarrow 3d^{10}4f^{n} + h\nu$ xray emission suggesting that the probability of direct recombination is significant. Under electron excitation 3ddirect-recombination emission is even less easily separated from Auger emission than in the case of 4d excitation, because the $3d \rightarrow 4f$ transition energies are generally below the corresponding 3d ionization thresholds. Ce is a potential exception to this pattern. Assuming a dominantly $4f^1$ configuration for the ground state of Ce metal (γ phase) it should be possible to observe the direct-recombination (DR) channel

$$3d^94f^2 \rightarrow 3d^{10}4f^0 + \epsilon l \tag{3}$$

because in that case there is no comparable Auger channel. The predicted emission energies $E_{3/2}^{DR}$ (5/2) are

$$E_{3/2}^{DR} = E_{3/2} = W_{4f}$$
,

where $E_{3/2}$ (5/2) are the main dipole-allowed $3d_{3/2}$ and $3d_{5/2}$ excitation energies observed for relatively high incident electron energies, and W_{4f} is the 4f binding energy (see Table I). Direct-recombination processes of type

$$3d^94f^2V \rightarrow 3d^{10}4f^1V^{-1} + \epsilon l \tag{4}$$

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are also possible, and will be in competition with Auger transitions of type

$$3d^94f^1V \rightarrow 3d^{10}4f^0V^{-1} + \epsilon l \tag{5}$$

$$\rightarrow 3d^{10}4f^1V^{-2} + \epsilon l \tag{6}$$

in a similar energy region. Assuming zero effective Coulomb interaction the predicted Auger energies of these processes are then $\sim 2 \text{ eV}$ below the $3d_{3/2}(5/2)$ ionization energies (Table I). Although the matrix elements for such transitions involving one or more conduction electrons are

likely to be smaller than for the pure 4f directrecombination channel, it is necessary to eliminate these possibilities empirically. One is able to achieve such discrimination by comparing emission at electron kinetic energies just below the 3d ionization energies both in Ce and La. In Ce channels Eqs. (3)-(6) are all open, while in La the process we are investigating (3) is absent, and process (5) corresponds to a direct-recombination channel, which accompanies the Auger channel

$$3d^{9}4f^{0}V \rightarrow 3d^{10}4f^{0}V^{-2} + \epsilon l$$
 (7)

A potential problem in the interpretation of such exper-

TABLE I. Estimates of direct-recombination emission energies and Auger energies for elemental Ce and La from empirical binding-energy and excitation energy data.

Excitation energies ^a			Energy (eV)		
· · · · · · · · · · · · · · · · · · ·			La $(n = 0)$	Ce $(n = 1)$	
$3d^{10}4f^n \rightarrow (3d^9)_{5/2}4f^{n+1}$	-1		835	882	
$\rightarrow (3d^9)_{3/2}4f^{n+1}$	-1		851	900	
Binding energies XPS			0.1	0.1	
V			0-1	0-1	
4 <i>f</i>			105	20	
4 <i>d</i>			105	109	
$3d_{5/2}$			836.1	884.2	
$3d_{3/2}$			852.9	902.7	
$U_{\rm eff}$ 4 <i>d</i> -4 <i>f</i> (estimated)			6	6	
4d-V (estimated)			0	0	
Appearance potential	spectroscopy				
$3d^{10} \perp e \rightarrow (3d^9) \cdot a^4f^2$	peeceopy		837d		
$3d + e \rightarrow (3d^9) + Af^2$		1	853°		
\rightarrow (3 <i>u</i>) _{3/2} + <i>j</i>			855		Ca
Direct recombination				Calculated	Experimental
$(3d^9)_{a} = 4d^{10}Af^{n+1}V$	$3d^{10}dd^{10}df^{n-1}V$			898	896
(54)3/274 75	$\rightarrow 3d^{10}d^{10}d^{10}d^{10}d^{10}$	850		800	0,00
	$\rightarrow 3d^{10}Ad^{9}Af^{n}V$	746		701	
$(2d^9)$ $Ad^{10}Af^{n+1}V$	$\rightarrow 3a + a + j = v$ 2a + 10a + 10a + n - 1 V	/40		791 880	880
(3 <i>a</i>) _{5/2} + <i>a</i> + <i>j v</i>	$\rightarrow 3a$ 4a 4j V $2a^{10}aa^{10}af^{11}z^{-1}$	021		800	880
	$\rightarrow 3a^{-4}a^{-4}f^{-1}v$	834		772	
	$\rightarrow 3a^{**}4a^{*}4j^{**}v$	/30		113	
Auger				Calculated	Experimental
$M_4 N_{67} V$				900	
M_4VV		852		901	
$M_4N_{45}N_{67}$				78 7	788
MANASV		$747^{\rm f}$		793 ^f	
$M_4 N_{45} O_{23}$		726 ^f		$768^{\rm f}$	770
$M_4 N_{45} O_1$		708		752	754
$M_5 N_{67} V$				881	· · · · ·
M ₅ VV		834		882	
M5N45N67				768	770
$M_5N_{45}V$		729		774	
$M_5N_{45}O_{23}$		709 ^f		750 ^f	754
$M_5N_{45}O_1$		691 ^f		734 ^f	739
			• 		

Reference 11.

^bReference 22.

^cReference 23.

^dReference 2 and 19.

^eEstimated from Ref. 2 and the 3d spin-orbit splitting.

^fEstimates of Ref. 24.

iments is ambiguity in the number of 4f electrons particularly in the excited state. Fuggle *et al.*¹⁶ have shown the importance of this phenomenon in x-ray absorption of rare-earth alloys; in elemental metals it is not significant, but in CeO₂ we shall show that similar effects occur.

The experimental setup to investigate these effects is as discussed by Matthew *et al.*¹⁰ in studying 4*d* direct recombination in Ce. The electron-emission spectra were recorded under UHV conditions by a concentric hemispherical analyzer with energy resolution ~ 0.5 eV, and sample Fermi-level reference. A linear background has

been subtracted from the spectra shown. Clean La and Ce were evaporated from a tungsten coil on the Mo substrates under ambient pressures $< 10^{-10}$ Torr, the pressure rising to $\le 10^{-9}$ Torr under evaporation. No impurity Auger signals were detectable on freshly evaporated films. Oxidation to the tetravalent CeO₂ state was achieved by prolonged dosage of O₂ with a stationary O₂ pressure of $\sim 10^{-8}$ Torr maintained in the spectrometer chamber during spectral accumulation. The resulting oxide phase was unambiguously identified as CeO₂-like by its 4*d* excitation spectrum.¹⁷



FIG. 1. Electron emission N(E) following electron-induced excitation in the kinetic energy region of the $3d_{3/2}$ and $3d_{5/2}$ binding energies. (a) clean Ce metal and CeO₂; (b) clean La—note the dips rather than peaks in the electron-energy distribution.

Figure 1 compares electron emission from clean Ce and La in the kinetic energy range around their respective 3dbinding energies. In the case of clean Ce metal [Fig. 1(a)] weak emission is observed near the $3d^94f^2 \rightarrow 3d^{10}4f^0$ direct-recombination emission energies, but for La no corresponding features are found [Fig. 1(b)]. Instead very small dips in emission are seen just above the $3d_{3/2}$ and $3d_{5/2}$ ionization thresholds: This probably corresponds to a "disappearance-potential" effect¹⁸ in which electrons leaving the solid are preferentially removed from the background at energies corresponding to the appearancepotential excitations seen by Kański et al.^{2,19} The Auger processes of type $3d^94f^1V \rightarrow 3d^{10}4f^0V^{-1}$, which are possible for Ce, but can occur as direct recombination in La, are predicted to occur at slightly higher energies than for the $3d^94f^2 \rightarrow 3d^{10}4f^0$ direct-recombination channel (Table I), but appear not to be of importance. This is consistent with the trend noted by Gerken and co-workers^{6,9} for 4d resonant photoemission, where conduction-bandelectron contributions to the partial ionization cross sections were substantially less than for the 4f channel. The contrast in behavior of Ce and La appears to confirm that the emission in Ce is mainly due to direct recombination

involving only 4f electrons.

Figure 1(a) also shows the direct-recombination spectrum of heavily oxidized Ce [in the form of CeO₂ (Ref. 17)]. The strong similarity between clean Ce and CeO_2 is at first sight surprising in that nominally tetravalent Ce (with ground-state configuration mainly $4f^0$) might be expected to behave like La. However, recent studies¹⁷ suggest that the main 3d excitation state of CeO₂ may correspond to a $3d^{9}4f^{2}$ -like final state through 4f screening by 4f-O_{2p} mixing. The emission from oxidized La (not shown) differs little from the clean metal, so this suggests that 3d emission in CeO₂ is not of the same type as the interatomic processes observed in the 4d emission of heavily oxidized lanthanum.¹² Further support for this view comes from the similarity of 4d emission of Ce metal¹⁰ and CeO_2 .¹¹ The direct-recombination experiment presented here suggests that the state following 3d excitation is very different for La and tetravalent Ce, and gives support to the 4f screening hypothesis in CeO₂. It should be mentioned that these experiments do not explicitly give information on the ground state of CeO_2 , but that they are not inconsistent with recent theoretical descriptions of CeO₂.^{20,21}



FIG. 2. Auger and direct-recombination electron emission of clean Ce in the region of $M_{4,(5)}N_{4,5}X$ transitions with X = (V, 4f, 5p, 5s).

The main Auger emission channels following 3d ionization in La (n=0) and Ce (n=1) involve creating a 4d hole:

$$3d^{9}4d^{10}5s^{2}5p^{6}4f^{n}V \rightarrow 3d^{10}4d^{9}5s^{2}5p^{6}4f^{n-1}V + \epsilon l \quad (8)$$

$$3d^{10}4d^95s^{2}5p^64f^nV^{-1}\epsilon l$$
, (9)

with process (8) absent for La. Given that direct recombination has been isolated above for the case of Ce, it seems likely that direct-recombination emission of type

$$3d^{9}4d^{10}5s^{2}5p^{6}4f^{n+1}V \rightarrow 3d^{10}4d^{9}5s^{2}5p^{6}4f^{n}V + \epsilon l$$
(10)

will also occur both in La and Ce, along with other channels in which the excited 4f electron is a spectator, e.g.,

$$3d^{9}4d^{10}5s^{2}5p^{6}4f^{n+1} \rightarrow 3d^{10}4d^{9}5s^{2}5p^{5}4f^{n+1} + \epsilon l \quad (11)$$

Making plausible assumptions about the effective Coulomb interaction ($\sim 6 \text{ eV}$) between 4d and 4f electrons, the Auger transitions are predicted to occur at energies very similar to those of competing directrecombination channels (Table I), and it is not possible to separate clearly the two processes in the observed emission spectrum (Fig. 2). Comparison with the corresponding emission obtained under nonresonant x-ray excitation would be needed to make an unambiguous assignment, but a substantial contribution from direction recombination seems likely. Similarly Auger emission and direct recombination involving 5p and 5s electrons will overlap.

This investigation highlights the advantages and disadvantages of studying nonradiative de-excitation processes using electron excitation. Much more incident flux is

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available than for tunable photon sources when the binding energy is > 500 eV, but, because electron impact lacks the selective excitation of resonant photon excitation, it is possible to isolate the direct recombination from Auger emission in only a limited number of cases.

In summary, comparison of electron emission following electron-excited 3d core-hole creation in La and Ce confirms the presence of weak $3d^94f^2 \rightarrow 3d^{10}4f^0 + \epsilon l$; direct recombination; the 3d Auger spectra of Ce and La contains emission from a variety of direct-recombination processes. The work presented here predicts that resonant photoemission should be observable in the 4d, 5p, and 4f channels in Ce for photon energies corresponding to the 3d photoabsorption. Electron-excited direct-recombination emission appears to provide a useful way of distinguishing $4f^1$ and $4f^2$ final configurations, and results for CeO₂ give support for a $3d^9 4f^2$ contribution in the excited state.

Note added in proof. Allen et al. have recently observed resonant enhancement of 4f photoemission at the 3d absorption edge of CeAl and TbCo₂, i.e., the photonexcited analog of the direct-recombination phenomenon presented here [J. W. Allen, S.-J. Oh, I. Lindau, and L. I. Johansson, Phys. Rev. B 29, 5927 (1984)].

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